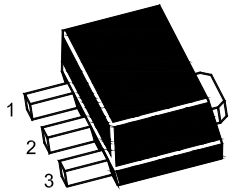
2SC4672U-H4031

NPN Silicon Epitaxial Planar Transistor

Low Frequency Transistor



1.Base 2.Collector 3.Emitter

SOT-89 Plastic Package

Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current - DC Collector Current - Pulse [1]	I_C I_{CP}	3 6	A
Total Power Dissipation	P_{tot}	0.5 2 [2]	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	- 55 to + 150	℃

[1] Single pulse, PW = 10 ms.

[2] When mounted on a 40 X 40 X 0.7 mm ceramic board.

Characteristics at T_a = 25℃

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE} = 2 V, I_C = 0.5 A at V_{CE} = 2 V, I_C = 1.5 A	 h_{FE} h_{FE}	 120 45	 - -	 270 -	 - -
Collector Base Cutoff Current at V_{CB} = 60 V	I_{CBO}	-	-	100	nA
Emitter Base Cutoff Current at V_{EB} = 5 V	I_{EBO}	-	-	100	nA
Collector Base Breakdown Voltage at I_C = 50 µA	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at I_C = 1 mA	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at I_E = 50 µA	$V_{(BR)EBO}$	6	-	-	V
Collector Emitter Saturation Voltage at I_C = 1 A, I_B = 50 mA	$V_{CE(sat)}$	-	-	0.35	V
Transition Frequency at V_{CE} = 5 V, $-I_E$ = 0.5 A, f = 100 MHz	f_T	-	210	-	MHz
Output Capacitance at V_{CB} = 10 V, f = 1 MHz	C_{ob}	-	25	-	pF

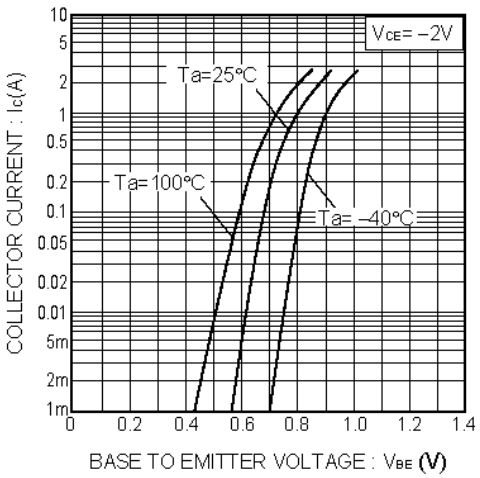


Fig.1 Grounded emitter propagation characteristics

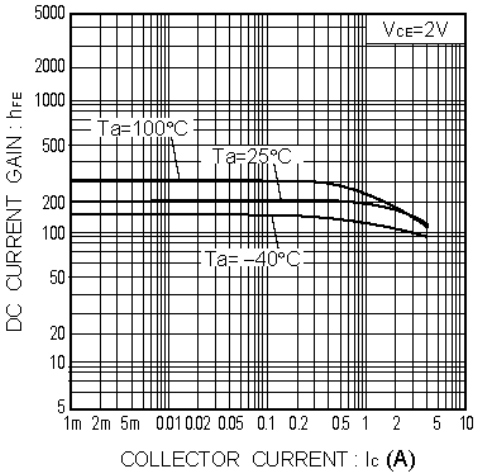


Fig.2 DC current gain vs. collector current

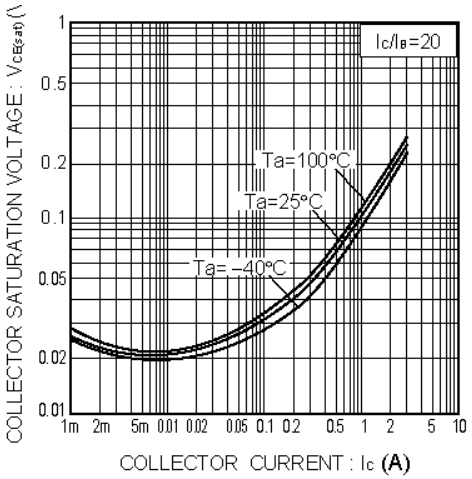


Fig.3 Collector-emitter saturation voltage vs. collector current

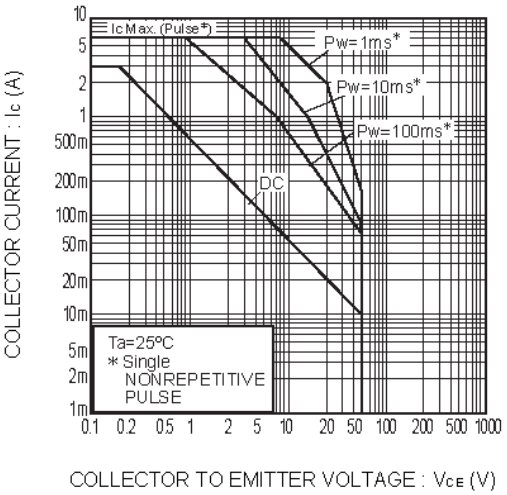
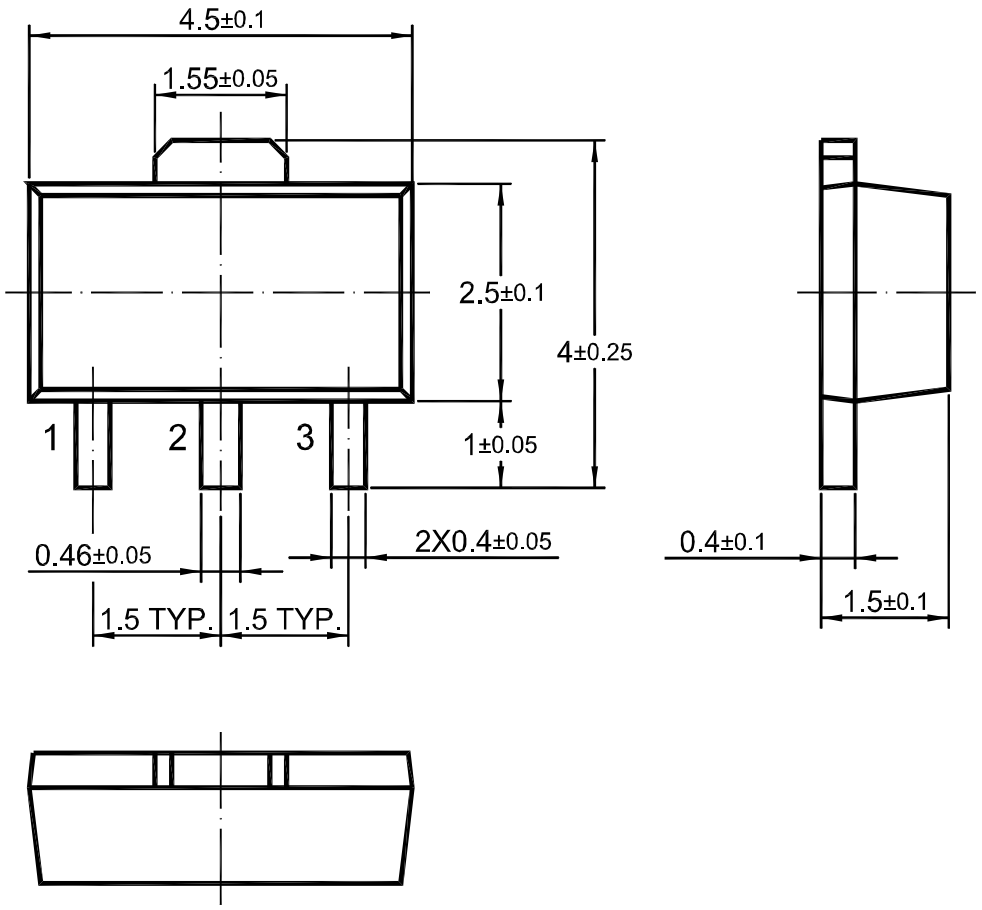


Fig.4 Safe Operating area

SOT-89 PACKAGE OUTLINE



Dimensions in mm